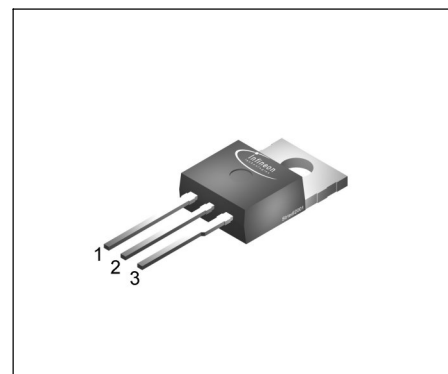


BUZ 73AL H

SIPMOS[®] Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated
- Logic Level
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



| Pin 1 | Pin 2 | Pin 3 |
|-------|-------|-------|
| G | D | S |

| Type | V _{DS} | I _D | R _{DS(on)} | Package | Pb-free |
|-------------|-----------------|----------------|---------------------|------------|---------|
| BUZ 73 AL H | 200 V | 5.5 A | 0.6 Ω | PG-TO220-3 | Yes |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|---------------|------|
| Continuous drain current $T_C = 37\text{ °C}$ | I_D | 5.5 | A |
| Pulsed drain current $T_C = 25\text{ °C}$ | I_{Dpuls} | 22 | |
| Avalanche current, limited by T_{jmax} | I_{AR} | 7 | |
| Avalanche energy, periodic limited by T_{jmax} | E_{AR} | 6.5 | mJ |
| Avalanche energy, single pulse $I_D = 7\text{ A}$, $V_{DD} = 50\text{ V}$, $R_{GS} = 25\text{ Ω}$ $L = 3.67\text{ mH}$, $T_j = 25\text{ °C}$ | E_{AS} | 120 | |
| Gate source voltage | V_{GS} | ± 20 | V |
| ESD-Sensitivity HBM as per MIL-STD 883 | | Class 1 | |
| Power dissipation $T_C = 25\text{ °C}$ | P_{tot} | 40 | W |
| Operating temperature | T_j | -55 ... + 150 | °C |
| Storage temperature | T_{stg} | -55 ... + 150 | |
| Thermal resistance, chip case | R_{thJC} | ≤ 3.1 | K/W |
| Thermal resistance, chip to ambient | R_{thJA} | 75 | |
| DIN humidity category, DIN 40 040 | | E | |
| IEC climatic category, DIN IEC 68-1 | | 55 / 150 / 56 | |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Static Characteristics

| | | | | | |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-----|-----------|----------|---------------|
| Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 25^\circ\text{C}$ | $V_{(BR)DSS}$ | 200 | - | - | V |
| Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$ | $V_{GS(th)}$ | 1.2 | 1.6 | 2 | |
| Zero gate voltage drain current $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25^\circ\text{C}$ $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125^\circ\text{C}$ | I_{DSS} | - | 0.1 10 | 1 100 | μA |
| Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$ | I_{GSS} | - | 10 | 100 | nA |
| Drain-Source on-resistance $V_{GS} = 5\text{ V}$, $I_D = 3.5\text{ A}$ | $R_{DS(on)}$ | - | 0.5 | 0.6 | Ω |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Dynamic Characteristics

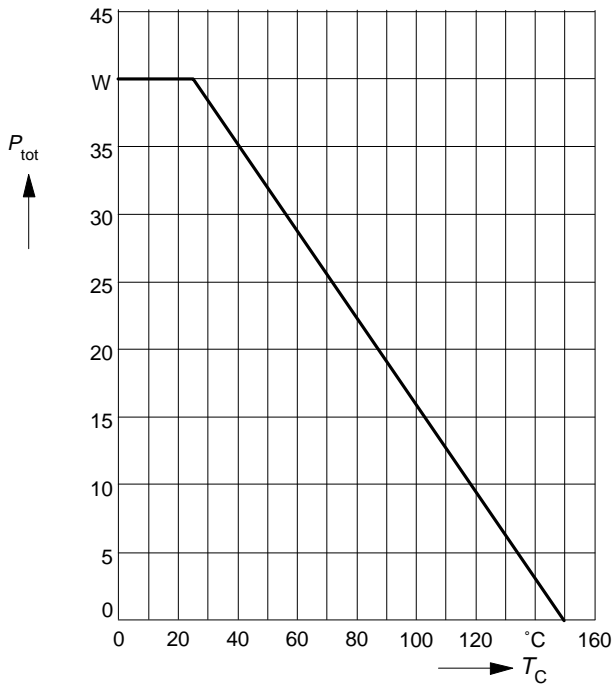
| | | | | | |
|-----------------------------------------------------------------------------------------------------------------------|--------------|---|-----|-----|----|
| Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 3.5 \text{ A}$ | g_{fs} | 5 | 6.5 | - | S |
| Input capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$ | C_{iss} | - | 630 | 840 | pF |
| Output capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$ | C_{oss} | - | 120 | 200 | |
| Reverse transfer capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$ | C_{rss} | - | 60 | 90 | |
| Turn-on delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 5 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$ | $t_{d(on)}$ | - | 15 | 20 | ns |
| Rise time $V_{DD} = 30 \text{ V}$, $V_{GS} = 5 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$ | t_r | - | 60 | 90 | |
| Turn-off delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 5 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$ | $t_{d(off)}$ | - | 100 | 130 | |
| Fall time $V_{DD} = 30 \text{ V}$, $V_{GS} = 5 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$ | t_f | - | 40 | 50 | |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|------------------------------------------------------------------------------------------------|----------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| Reverse Diode | | | | | |
| Inverse diode continuous forward current $T_C = 25^\circ\text{C}$ | I_S | - | - | 5.5 | A |
| Inverse diode direct current, pulsed $T_C = 25^\circ\text{C}$ | I_{SM} | - | - | 22 | |
| Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 14\text{ A}$ | V_{SD} | - | 1.1 | 1.7 | V |
| Reverse recovery time $V_R = 100\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | t_{rr} | - | 140 | - | ns |
| Reverse recovery charge $V_R = 100\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | Q_{rr} | - | 0.7 | - | μC |

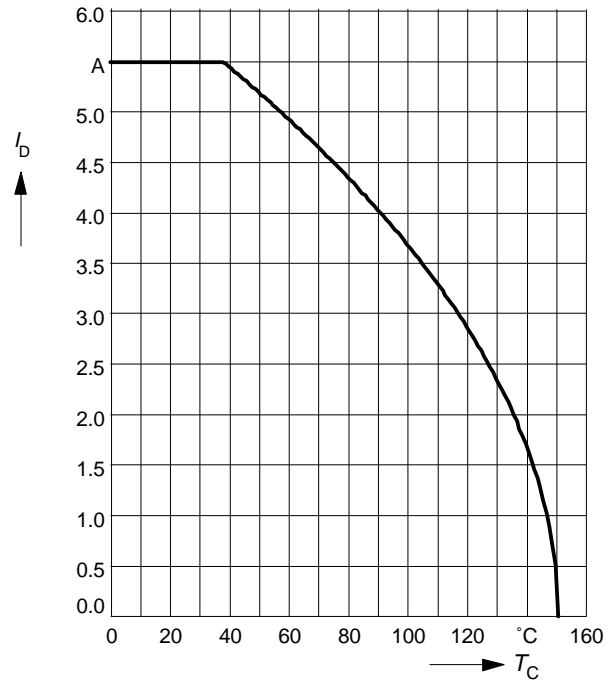
Power dissipation

$P_{tot} = f(T_C)$



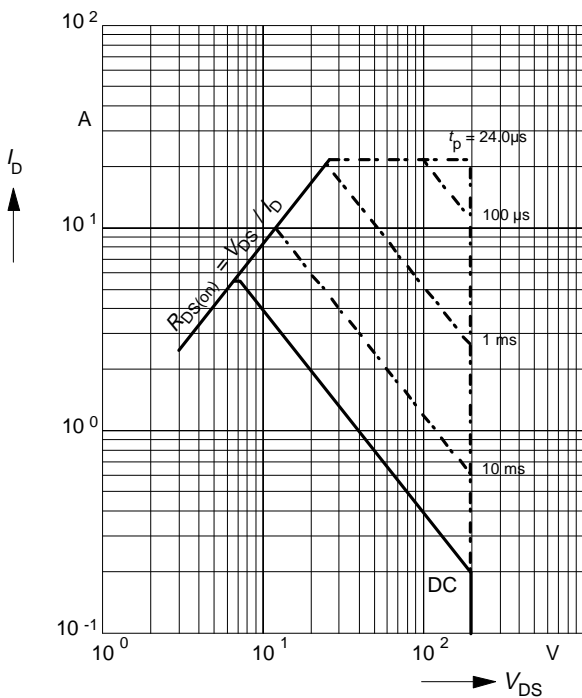
Drain current

$I_D = f(T_C)$
parameter: $V_{GS} \geq 5 \text{ V}$



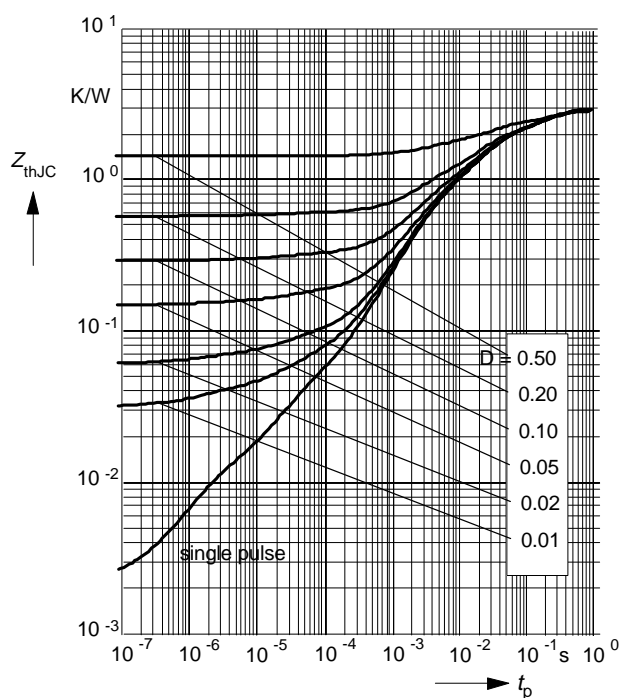
Safe operating area

$I_D = f(V_{DS})$
parameter: $D = 0.01, T_C = 25^\circ\text{C}$



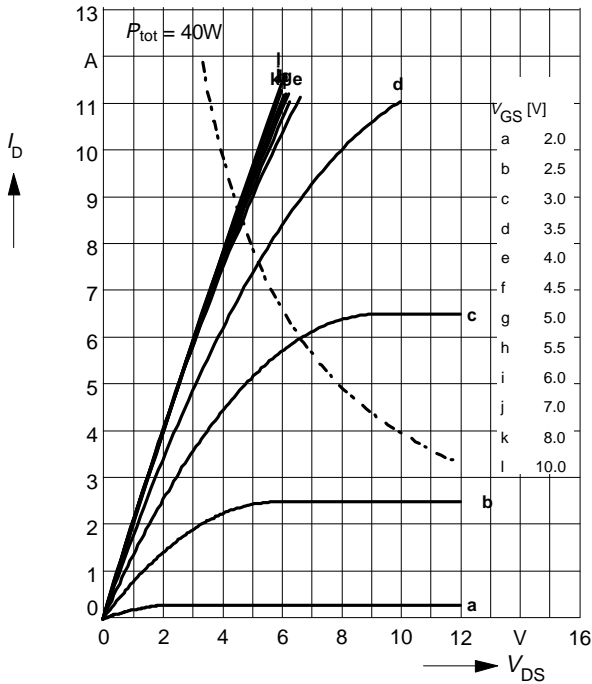
Transient thermal impedance

$Z_{thJC} = f(t_p)$
parameter: $D = t_p / T$

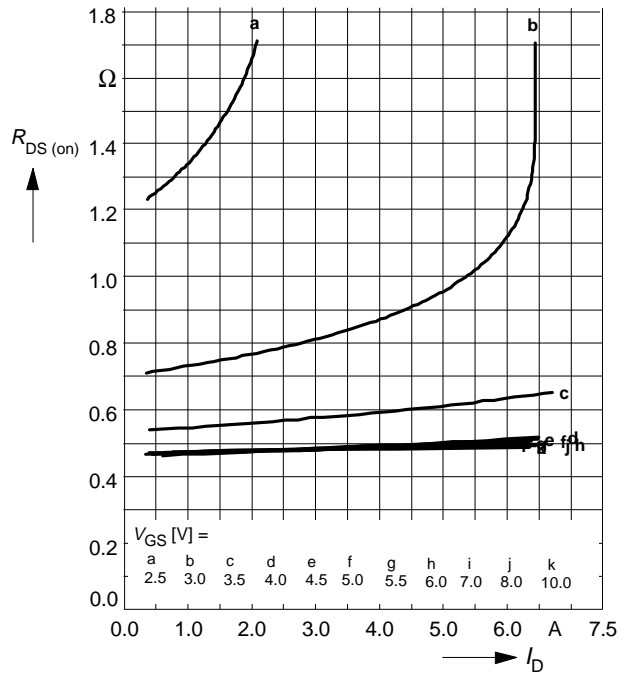


Typ. output characteristics

$$I_D = f(V_{DS})$$

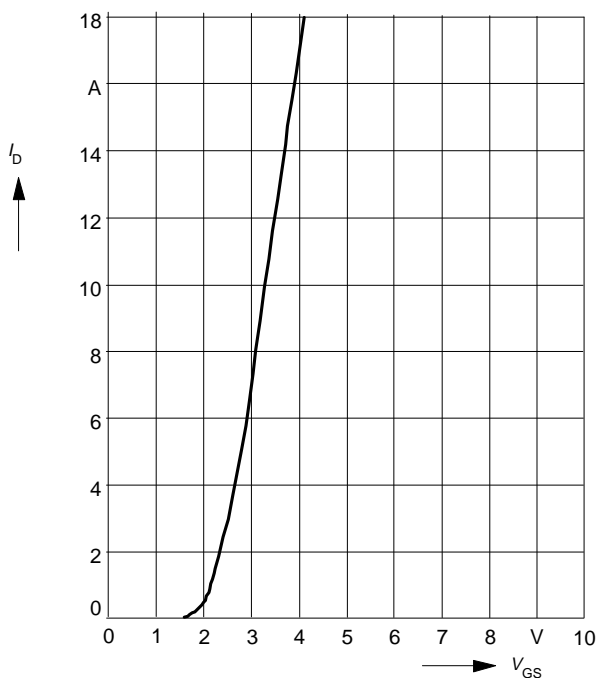
 parameter: $t_p = 80 \mu s$

Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

 parameter: V_{GS}

Typ. transfer characteristics $I_D = f(V_{GS})$

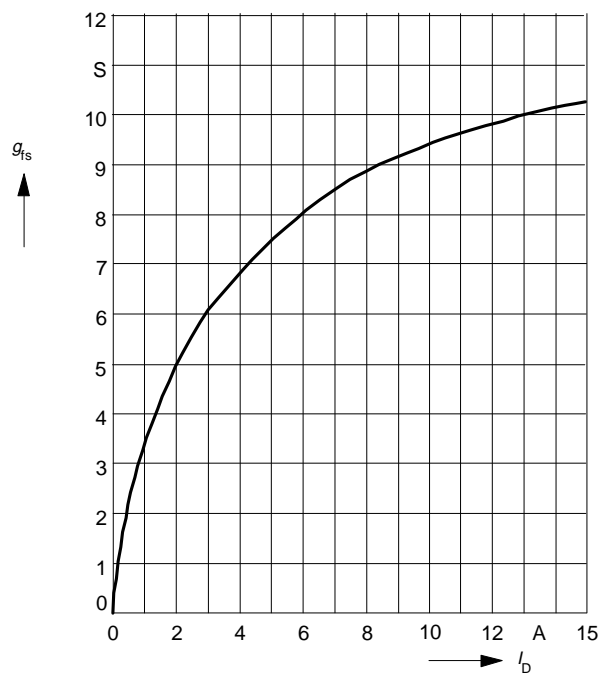
 parameter: $t_p = 80 \mu s$

$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$


Typ. forward transconductance $g_{fs} = f(I_D)$

 parameter: $t_p = 80 \mu s$,

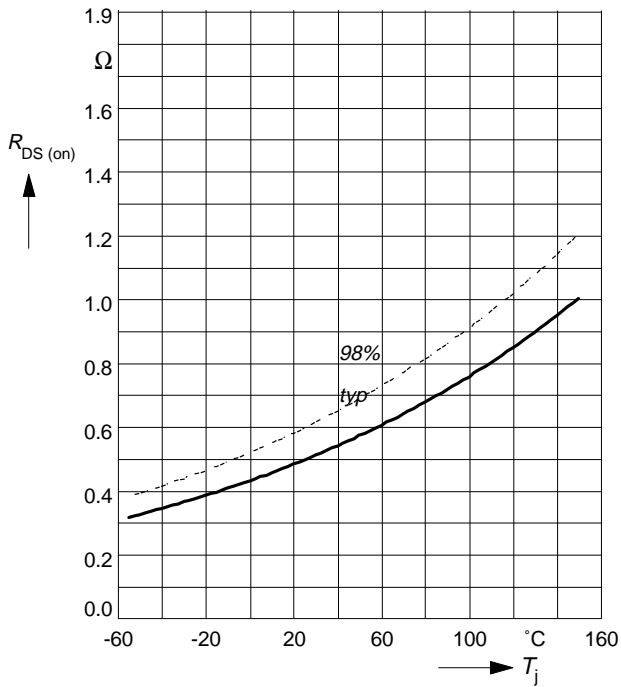
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

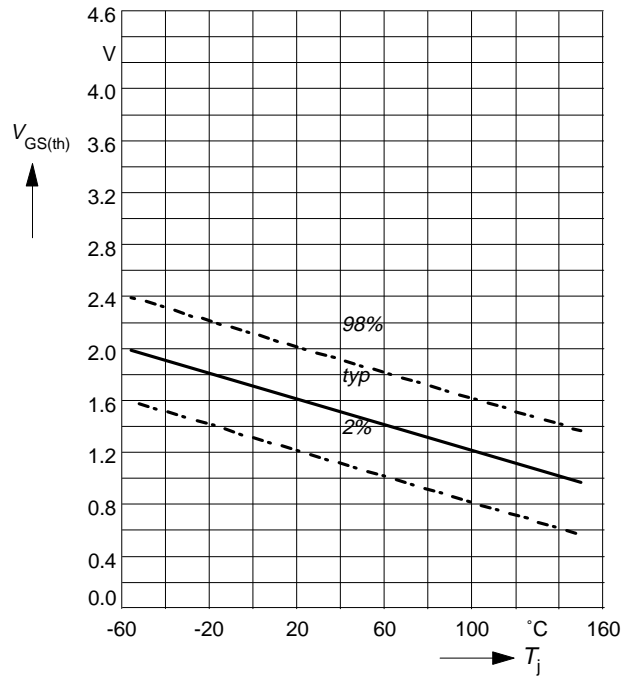
parameter: $I_D = 3.5\text{ A}$, $V_{GS} = 5\text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

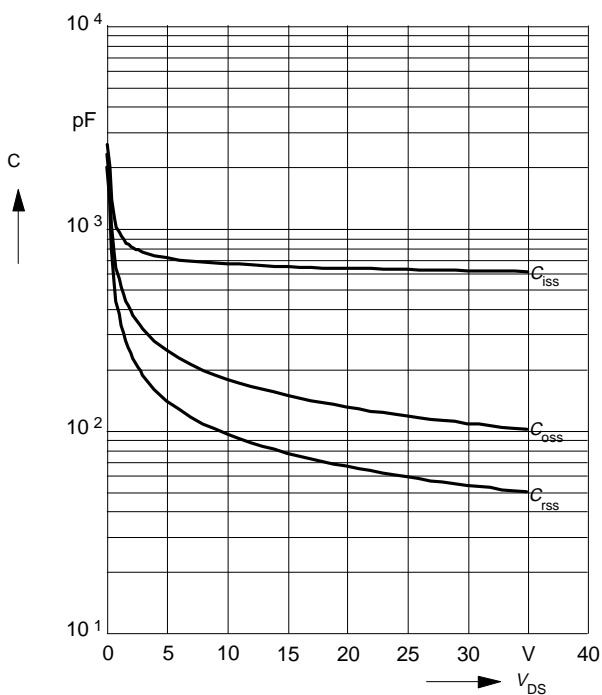
parameter: $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$



Typ. capacitances

$$C = f(V_{DS})$$

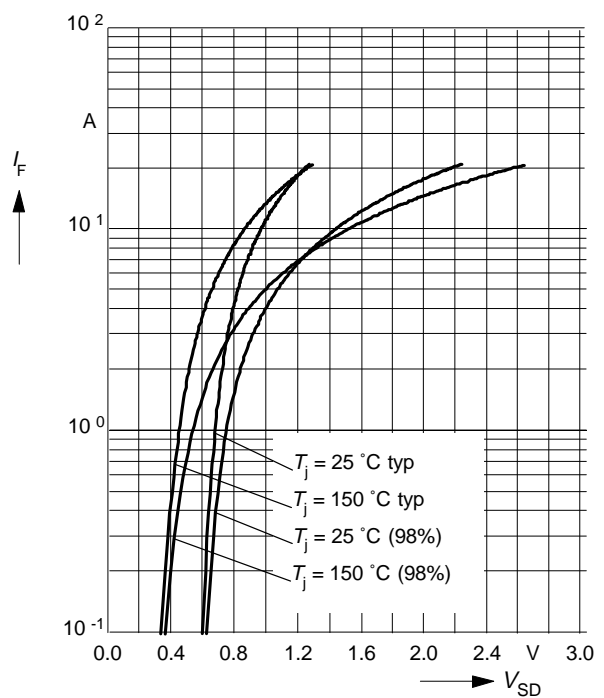
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



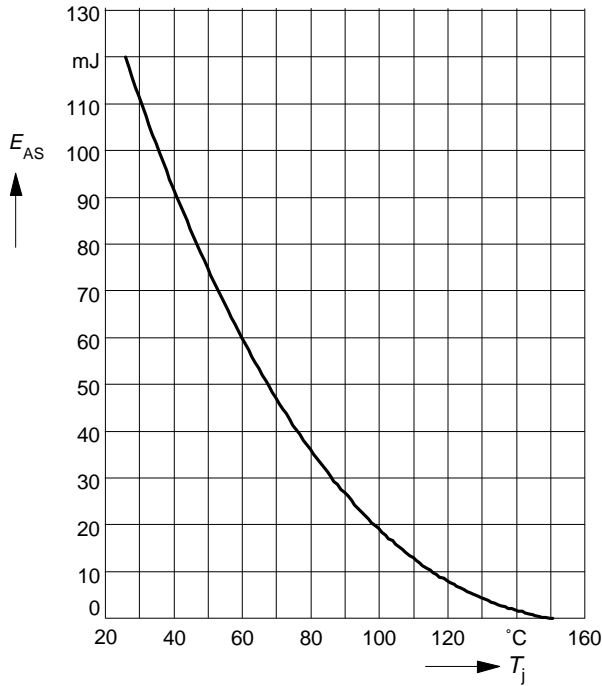
Forward characteristics of reverse diode

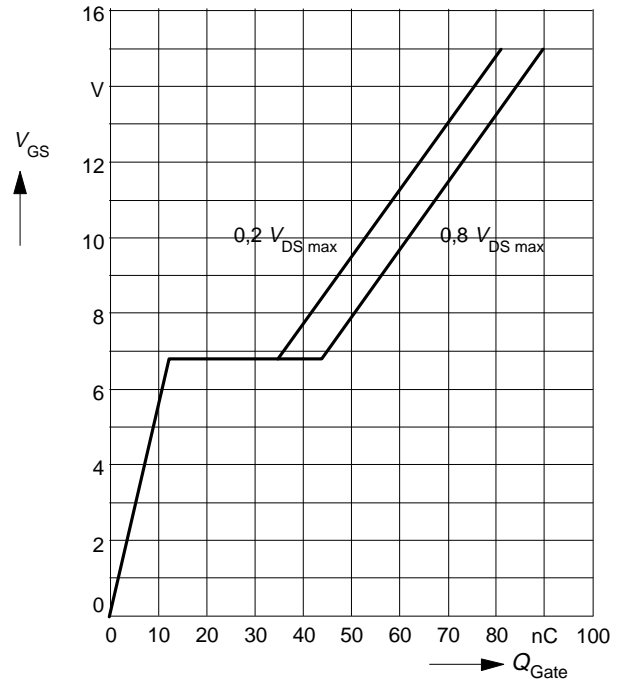
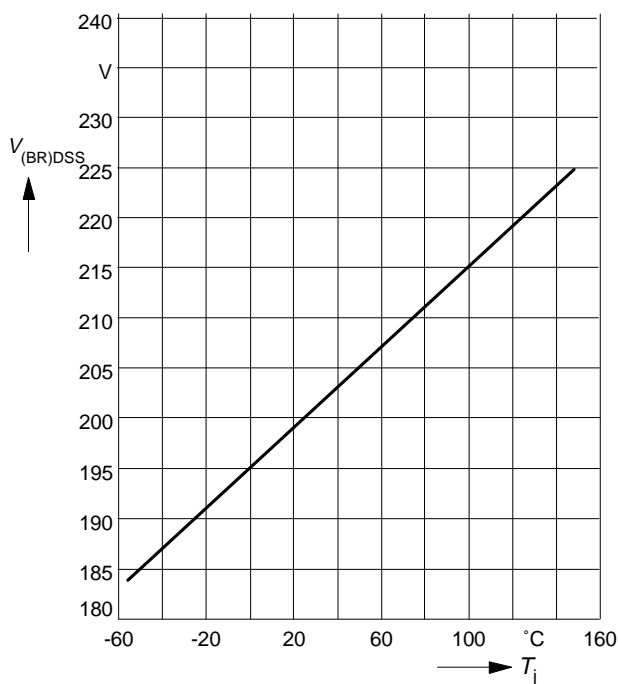
$$I_F = f(V_{SD})$$

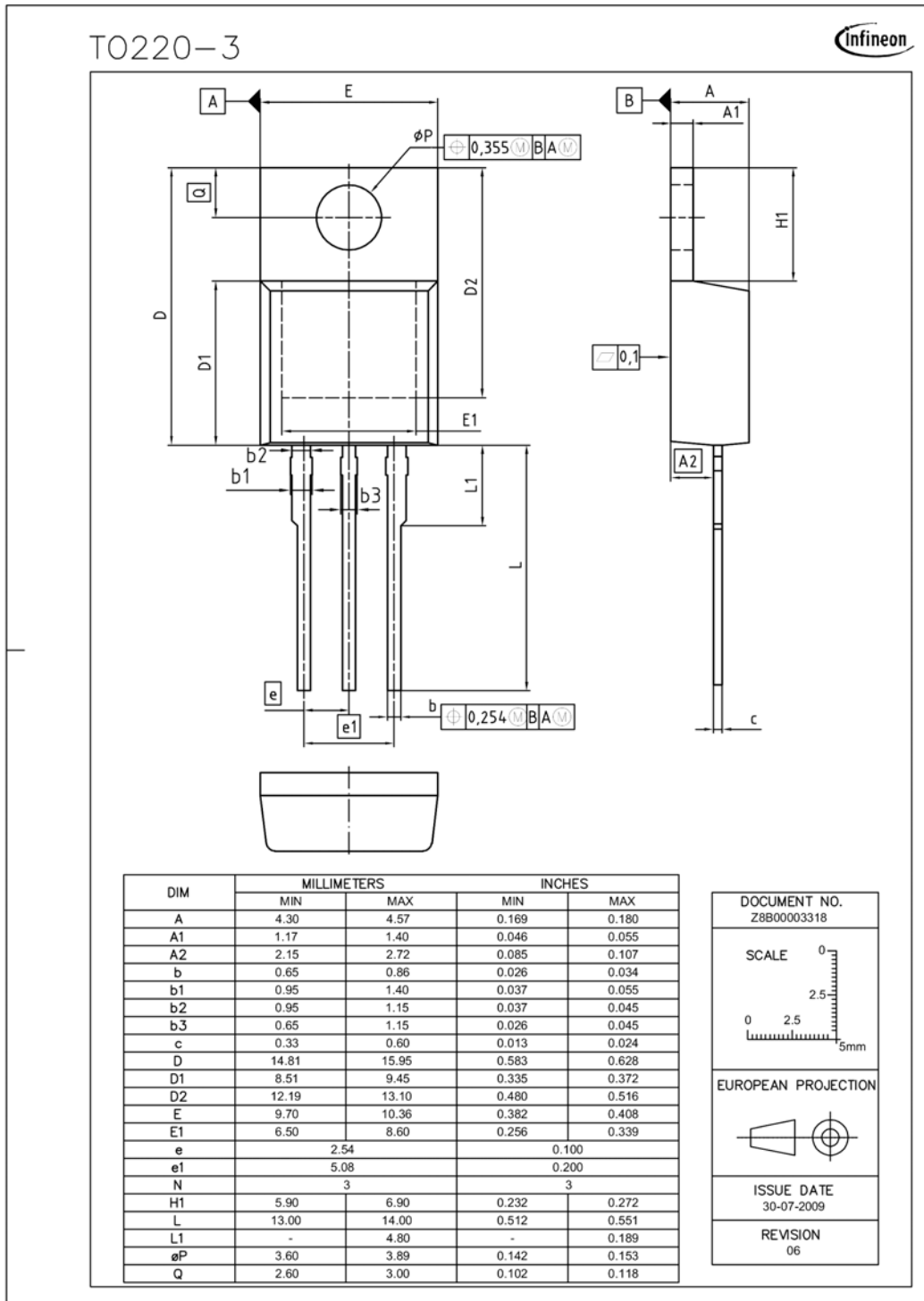
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



Avalanche energy $E_{AS} = f(T_j)$

 parameter: $I_D = 7\text{ A}$, $V_{DD} = 50\text{ V}$
 $R_{GS} = 25\ \Omega$, $L = 3.67\text{ mH}$

Typ. gate charge $V_{GS} = f(Q_{Gate})$
 $V_{GS} = f(Q_{Gate})$

 parameter: $I_{D\text{ puls}} = 63\text{ A}$

Drain-source breakdown voltage $V_{(BR)DSS} = f(T_j)$
 $V_{(BR)DSS} = f(T_j)$


Package Drawing: TO220-3


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